

REMARKS

In response to the Final Office Action in the above-referenced United States patent application, Applicants have set forth this preliminary amendment that modifies the claims in order to distinguish from the cited references of record. Applicants have modified claims 1, 8 and 12 to specify that an oxygen including layer is formed on the cobalt silicide. Claim 5 has also been modified to include limitations directed to the formation of the cobalt silicide layer in a silane gas system wherein the cobalt including layer is the cobalt source and the silane is the silicon source for the cobalt silicide. The prior art of record fails to provide an teaching or suggestion whatsoever concerning these devices or manufacturing processes. To the contrary, the prior art actual teaches away from the use of oxygen including layers. Applicants invention advantageously allows the use of conventional insulation layers such as SiO₂ in the manufacturing process. Furthermore, Applicants have provided new manufacturing techniques wherein the cobalt silicide can be advantageously formed in a very simple and convenient manner. Additionally, a silicon dioxide layer can be easily formed by modifying the processing techniques as specified. The art of record does not teach or suggest these innovations. Accordingly, in light of the foregoing, Applicants respectfully request that the Examiner withdraw the rejections and allow all claims in the application.

Respectfully submitted,

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Robert J. Depke

(Reg. #37,607)

HOLLAND & KNIGHT LLC
131 South Dearborn, 30th Floor
Chicago, Illinois 60603
Tel: (312) 422-9050
Attorney for Applicant